

OXIDATIVE CONDITIONING METHOD FOR METAL OXIDE
LAYER AND APPLICATIONS THEREOF

ABSTRACT OF THE DISCLOSURE

A metal oxide layer may be made more highly oxidized by exposing the layer to sulfur trioxide. The leakage current of the layer may thereby be decreased, providing a capacitor containing such a layer with improved performance properties. The capacitor may be incorporated into a dynamic random access memory cell or other structure useful in the semiconductor or other industry.